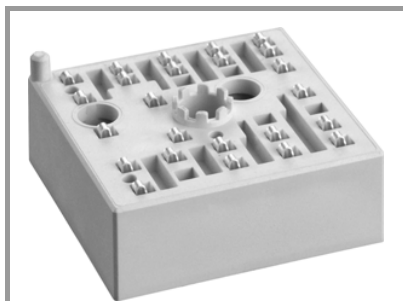


# SKiiP 11NAB12T4V1



MiniSKiiP® 1

## SKiiP 11NAB12T4V1

### Features

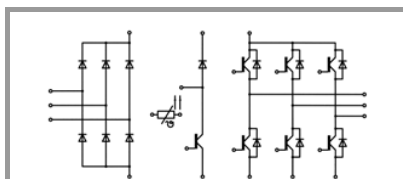
- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

### Typical Applications\*

- Inverter up to 8 kVA
- Typical motor power 4 kW

### Remarks

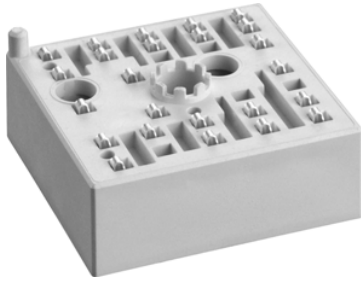
- $V_{CEsat}$ ,  $V_F$  = chip level value
- Case temp. limited to  $T_C = 125^\circ\text{C}$  max. (for baseplateless modules  $T_C = T_S$ )
- product rel. results valid for  $T_j \leq 150$  (recomm.  $T_{op} = -40 \dots +150^\circ\text{C}$ )



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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
<b>Inverter - IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$		1200	V
$I_C$	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	12	A
		$T_s = 70^\circ\text{C}$	12	A
$I_C$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	12	A
		$T_s = 70^\circ\text{C}$	12	A
$I_{Cnom}$			8	A
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$		24	A
$V_{GES}$			-20 ... 20	V
$t_{psc}$	$V_{CC} = 800\text{ V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
	$V_{GE} \leq 15\text{ V}$			
	$V_{CES} \leq 1200\text{ V}$			
$T_j$			-40 ... 175	$^\circ\text{C}$
<b>Chopper - IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$		1200	V
$I_C$	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	12	A
		$T_s = 70^\circ\text{C}$	12	A
$I_C$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	12	A
		$T_s = 70^\circ\text{C}$	12	A
$I_{Cnom}$			8	A
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$		24	A
$V_{GES}$			-20 ... 20	V
$t_{psc}$	$V_{CC} = 800\text{ V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
	$V_{GE} \leq 15\text{ V}$			
	$V_{CES} \leq 1200\text{ V}$			
$T_j$			-40 ... 175	$^\circ\text{C}$
<b>Inverse - Diode</b>				
$V_{RRM}$	$T_j = 25^\circ\text{C}$		1200	V
$I_F$	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	14	A
		$T_s = 70^\circ\text{C}$	11	A
$I_F$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	15	A
		$T_s = 70^\circ\text{C}$	12	A
$I_{Fnom}$			8	A
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$		24	A
$I_{FSM}$	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 150^\circ\text{C}$		36	A
$T_j$			-40 ... 175	$^\circ\text{C}$
<b>Freewheeling - Diode</b>				
$V_{RRM}$	$T_j = 25^\circ\text{C}$		1200	V
$I_F$	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	14	A
		$T_s = 70^\circ\text{C}$	11	A
$I_F$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	15	A
		$T_s = 70^\circ\text{C}$	12	A
$I_{Fnom}$			8	A
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$		24	A
$I_{FSM}$	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 150^\circ\text{C}$		36	A
$T_j$			-40 ... 175	$^\circ\text{C}$

# SKiiP 11NAB12T4V1



MiniSKiiP® 1

## SKiiP 11NAB12T4V1

### Features

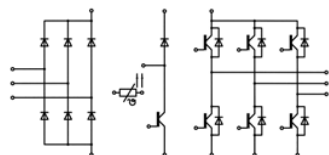
- Trench 4 IGBT's
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- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

### Typical Applications\*

- Inverter up to 8 kVA
- Typical motor power 4 kW

### Remarks

- $V_{CEsat}$ ,  $V_F$  = chip level value
- Case temp. limited to  $T_C = 125^\circ\text{C}$  max. (for baseplateless modules  $T_C = T_S$ )
- product rel. results valid for  $T_j \leq 150$  (recomm. Top =  $-40 \dots +150^\circ\text{C}$ )



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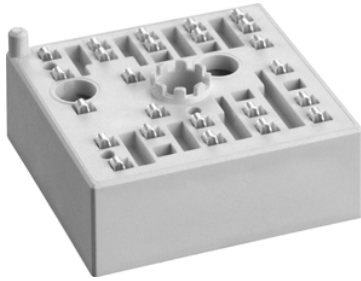
### Absolute Maximum Ratings

Symbol	Conditions	Values	Unit	
<b>Rectifier - Diode</b>				
$V_{RRM}$	$T_j = 25^\circ\text{C}$	1600	V	
$I_F$	$T_s = 25^\circ\text{C}, T_j = 150^\circ\text{C}$	39	A	
$I_{Fnom}$		8	A	
$I_{FSM}$	10 ms	$T_j = 25^\circ\text{C}$	220	A
	sin 180°	$T_j = 150^\circ\text{C}$	200	A
$I^2t$	10 ms	$T_j = 25^\circ\text{C}$	242	A <sup>2</sup> s
	sin 180°	$T_j = 150^\circ\text{C}$	200	A <sup>2</sup> s
$T_j$		-40 ... 150	°C	
<b>Module</b>				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}, 20\text{A per spring}$	20	A	
$T_{stg}$		-40 ... 125	°C	
$V_{isol}$	AC sinus 50Hz, 1 min	2500	V	

### Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
<b>Inverter - IGBT</b>					
$V_{CE(sat)}$	$I_C = 8\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$	1.85	2.10	V
		$T_j = 150^\circ\text{C}$	2.25	2.45	V
$V_{CE0}$		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	131	150	mΩ
		$T_j = 150^\circ\text{C}$	194	206	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1\text{ mA}$	5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
					mA
$C_{ies}$	$V_{CE} = 25\text{ V}$		0.49		nF
$C_{oes}$	$V_{GE} = 0\text{ V}$		0.05		nF
$C_{res}$			0.03		nF
$Q_G$	- 8 V...+ 15 V		45		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$		0.00		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	31		ns
$t_r$	$I_C = 8\text{ A}$	$T_j = 150^\circ\text{C}$	31		ns
$E_{on}$	$R_{G on} = 47\ \Omega$	$T_j = 150^\circ\text{C}$	0.87		mJ
$t_{d(off)}$	$R_{G off} = 47\ \Omega$	$T_j = 150^\circ\text{C}$	290		ns
		$T_j = 150^\circ\text{C}$	70		ns
$E_{off}$	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$	0.74		mJ
$R_{th(j-s)}$	per IGBT		1.84		K/W
<b>Chopper - IGBT</b>					
$V_{CE(sat)}$	$I_C = 8\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$	1.85	2.10	V
		$T_j = 150^\circ\text{C}$	2.25	2.45	V
$V_{CE0}$		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	131	150	mΩ
		$T_j = 150^\circ\text{C}$	194	206	mΩ
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1\text{ mA}$	5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
$Q_G$	- 8 V...+ 15 V		45		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$		0.00		Ω

# SKiiP 11NAB12T4V1



MiniSKiiP® 1

## SKiiP 11NAB12T4V1

### Features

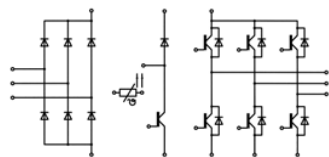
- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

### Typical Applications\*

- Inverter up to 8 kVA
- Typical motor power 4 kW

### Remarks

- $V_{CEsat}$ ,  $V_F$  = chip level value
- Case temp. limited to  $T_C = 125^\circ\text{C}$  max. (for baseplateless modules  $T_C = T_S$ )
- product rel. results valid for  $T_j \leq 150$  (recomm. Top =  $-40 \dots +150^\circ\text{C}$ )



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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Chopper - IGBT</b>						
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		31		ns
$t_r$	$I_C = 8\text{ A}$	$T_j = 150^\circ\text{C}$		31		ns
$E_{on}$	$R_{G\ on} = 47\ \Omega$	$T_j = 150^\circ\text{C}$		0.87		mJ
$t_{d(off)}$	$R_{G\ off} = 47\ \Omega$	$T_j = 150^\circ\text{C}$		290		ns
$t_f$		$T_j = 150^\circ\text{C}$		70		ns
$E_{off}$	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$		0.74		mJ
$R_{th(j-s)}$	per IGBT			1.84		K/W
<b>Inverse - Diode</b>						
$V_F = V_{EC}$	$I_F = 8\text{ A}$	$T_j = 25^\circ\text{C}$		2.3	2.6	V
	$V_{GE} = 0\text{ V}$ chiplevel	$T_j = 150^\circ\text{C}$		2.4	2.7	V
$V_{F0}$		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$		129	144	m $\Omega$
		$T_j = 150^\circ\text{C}$		181	198	m $\Omega$
$I_{RRM}$	$I_F = 8\text{ A}$	$T_j = 150^\circ\text{C}$		8.3		A
$Q_{rr}$	$di/dt_{off} = 380\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		1.35		$\mu\text{C}$
$E_{rr}$	$V_{GE} = -15\text{ V}$	$T_j = 150^\circ\text{C}$		0.57		mJ
	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-s)}$	per Diode			2.53		K/W
<b>Freewheeling - Diode</b>						
$V_F = V_{EC}$	$I_F = 8\text{ A}$	$T_j = 25^\circ\text{C}$		2.3	2.6	V
	$V_{GE} = 0\text{ V}$ chiplevel	$T_j = 150^\circ\text{C}$		2.4	2.7	V
$V_{F0}$		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$		129	144	m $\Omega$
		$T_j = 150^\circ\text{C}$		181	198	m $\Omega$
$I_{RRM}$	$I_F = 8\text{ A}$	$T_j = 150^\circ\text{C}$		8.3		A
$Q_{rr}$	$di/dt_{off} = 380\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		1.35		$\mu\text{C}$
$E_{rr}$	$V_{GE} = -15\text{ V}$	$T_j = 150^\circ\text{C}$		0.57		mJ
	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$				
$R_{th(j-s)}$	per Diode			2.53		K/W
<b>Rectifier - Diode</b>						
$V_F = V_{EC}$	$I_F = 8\text{ A}$	$T_j = 25^\circ\text{C}$		1	1.21	V
	$V_{GE} = 0\text{ V}$ chiplevel	$T_j = 125^\circ\text{C}$			1.1	V
$V_{F0}$		$T_j = 25^\circ\text{C}$			1.0	V
		$T_j = 125^\circ\text{C}$			0.8	V
$r_F$		$T_j = 25^\circ\text{C}$		15	29	m $\Omega$
		$T_j = 125^\circ\text{C}$			34	m $\Omega$
$R_{th(j-s)}$	per Diode			1.5		K/W
<b>Module</b>						
$M_s$	to heat sink		2		2.5	Nm
w				35		g
<b>Temperatur Sensor</b>						
$R_{100}$	$T_r = 100^\circ\text{C}$ , tolerance = 3 %			$1670 \pm 3\%$		$\Omega$
$R(T)$	$R(T) = 1000\Omega [1 + A(T - 25^\circ\text{C}) + B(T - 25^\circ\text{C})^2]$ ], $A = 7.635 \cdot 10^{-3}\text{ }^\circ\text{C}^{-1}$ , $B = 1.731 \cdot 10^{-5}\text{ }^\circ\text{C}^{-2}$					

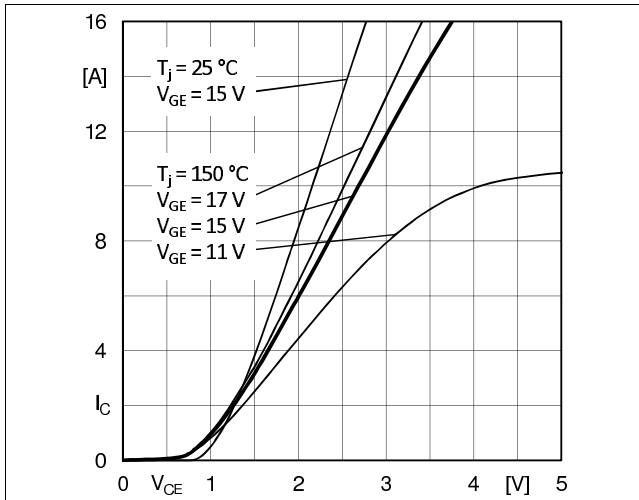


Fig. 1: Typ. output characteristic

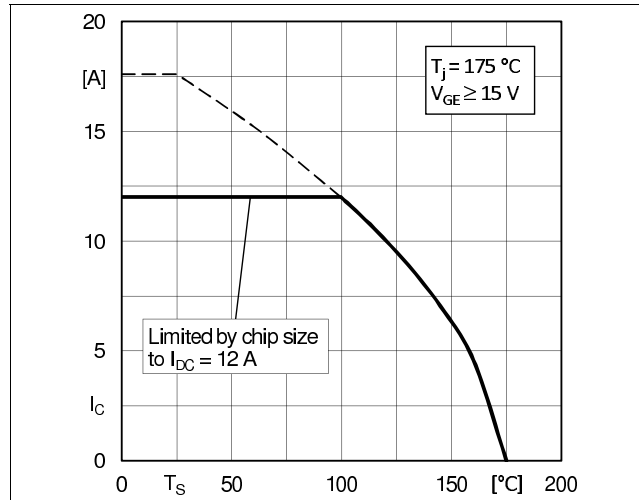


Fig. 2: Typ. rated current vs. temperature  $I_C = f(T_S)$

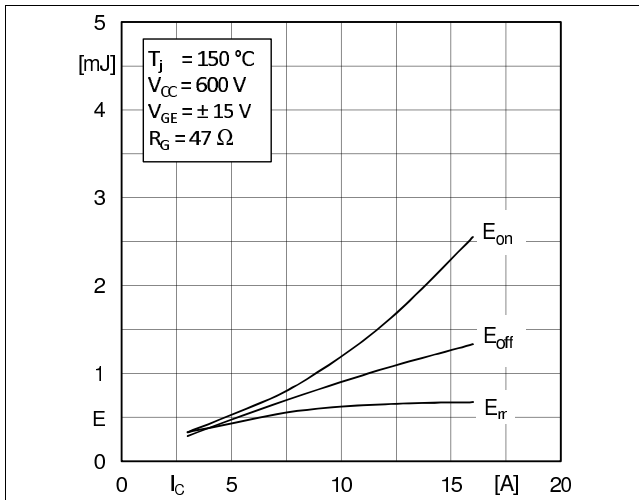


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

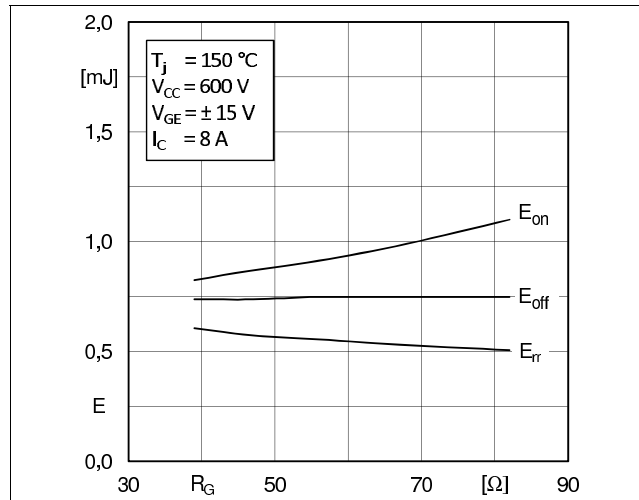


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

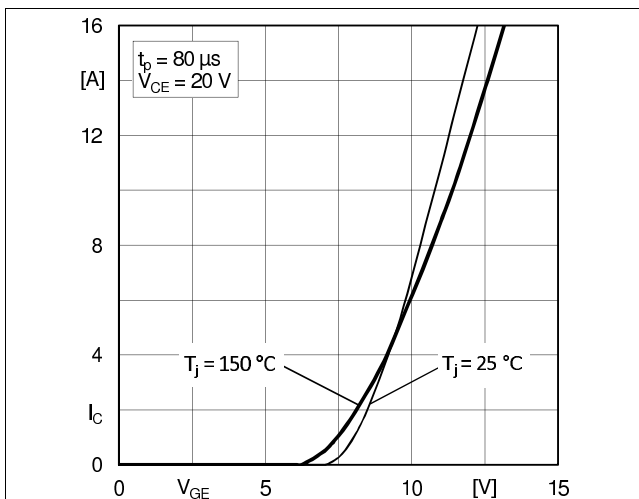


Fig. 5: Typ. transfer characteristic

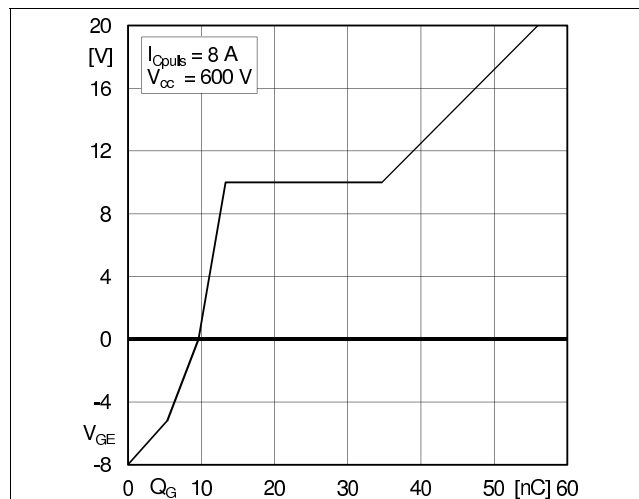


Fig. 6: Typ. gate charge characteristic

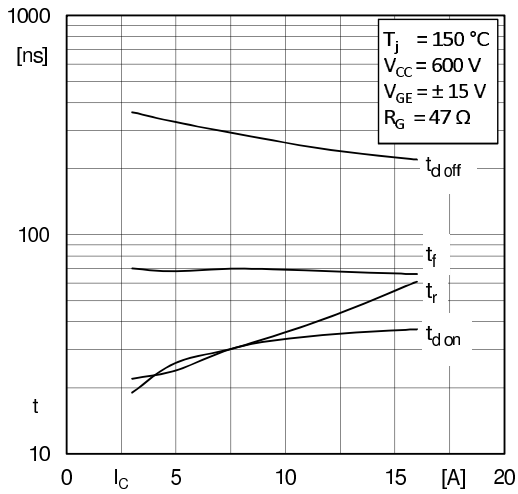


Fig. 7: Typ. switching times vs.  $I_C$

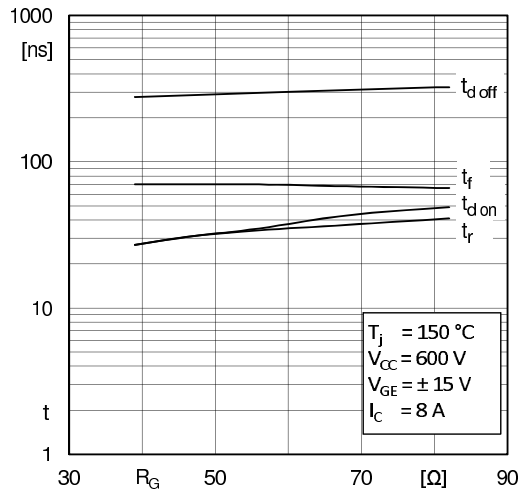


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

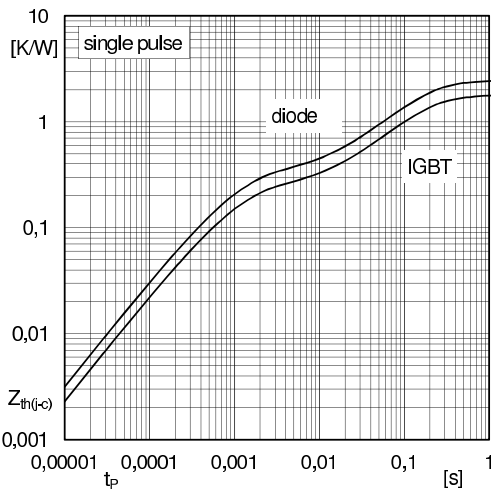


Fig. 9: Transient thermal impedance of IGBT and Diode

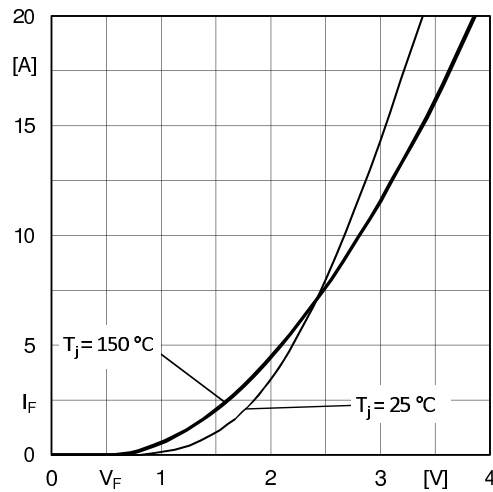


Fig. 10: CAL diode forward characteristic

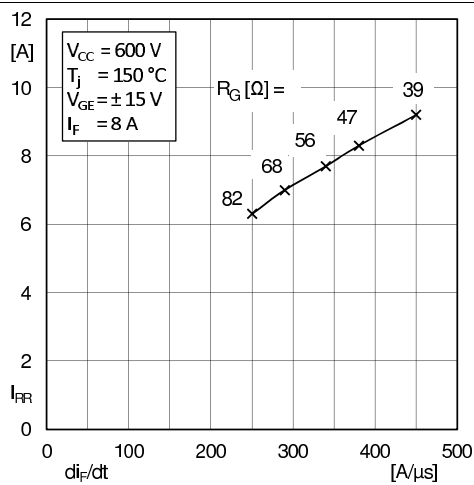


Fig. 11: Typ. CAL diode peak reverse recovery current

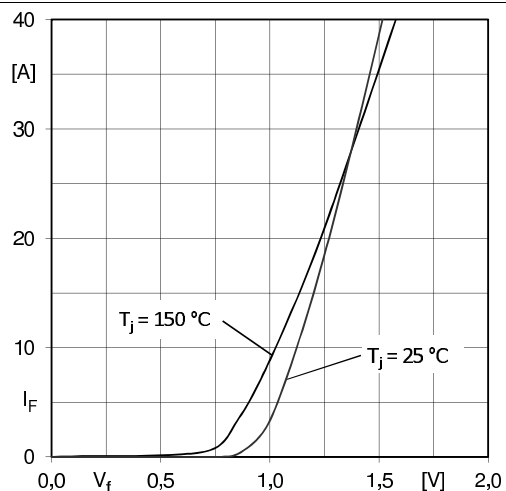
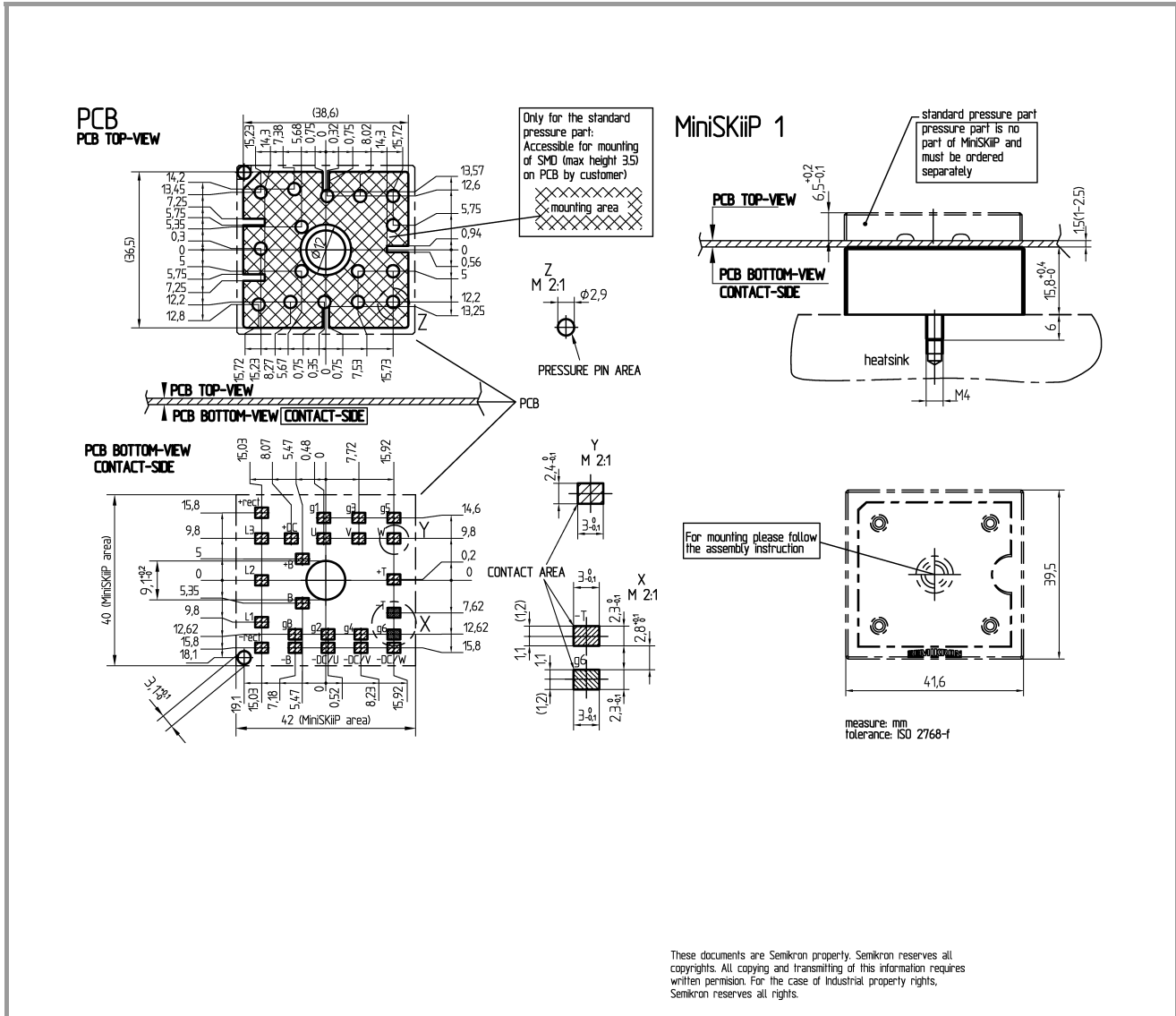
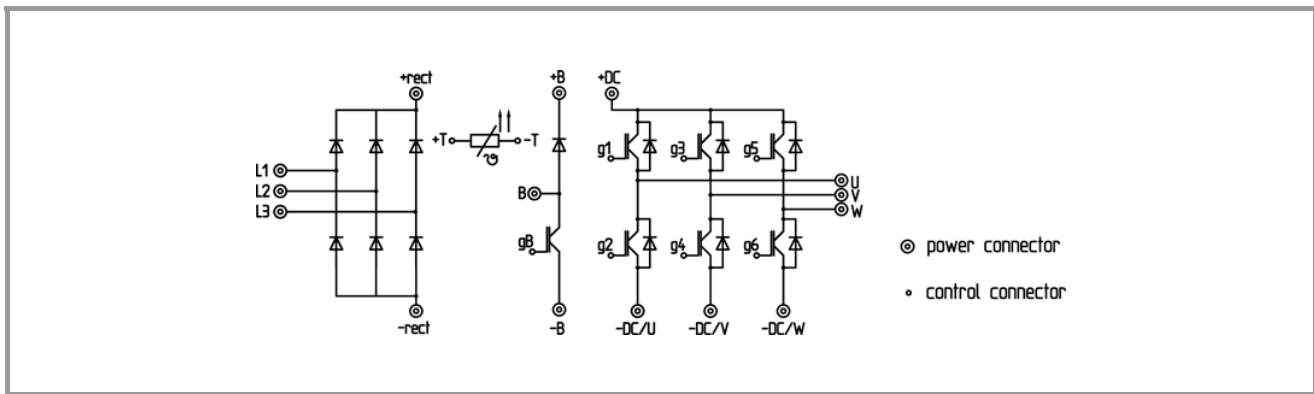


Fig. 12: Typ. input bridge forward characteristic



pinout, dimensions



pinout

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.